Product Preview Data Sheet

Insulated Gate Bipolar Transistor

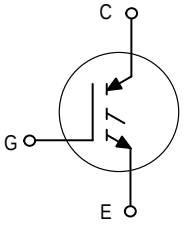
N–Channel Enhancement Mode Silicon Gate

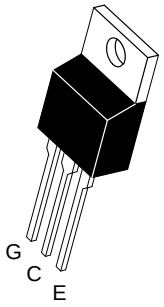
MGP5N60E

IGBT IN TO–220
5 A @ 90°C
6 A @ 25°C
600 VOLTS
SHORT CIRCUIT RATED
LOW ON–VOLTAGE

This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage blocking capability. Its new 600V IGBT technology is specifically suited for applications requiring both a high temperature short circuit capability and a low VCE(on). It also provides fast switching characteristics and results in efficient operation at high frequencies. This new E–series introduces an Energy–efficient and short circuit rated device.

- Industry Standard TO–220 Package
- High Speed E_{off}: 44 μJ/A typical at 125°C
- High Short Circuit Capability – 10 μs minimum at 125°C
- Low On–Voltage – 2.0V typical at 3A, 125°C
- Robust High Voltage Termination





CASE 221A–06, Style 9
TO–220AB

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	600	Vdc
Collector–Gate Voltage (R_{GE} = 1.0 MΩ)	V_{CGR}	600	Vdc
Gate–Emitter Voltage — Continuous	V_{GE}	±20	Vdc
Collector Current — Continuous @ T_C = 25°C — Continuous @ T_C = 90°C — Repetitive Pulsed Current (1)	I_{C25} I_{C90} I_{CM}	6 5 12	Adc Apk
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	62 0.50	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to 150	°C
Short Circuit Withstand Time (V_{CC} = 360 Vdc, V_{GE} = 15 Vdc, T_J = 125°C, R_G = 20 Ω)	t_{sc}	10	μs
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.01 65	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 5 seconds	T_L	260	°C
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)		

(1) Pulse width is limited by maximum junction temperature.

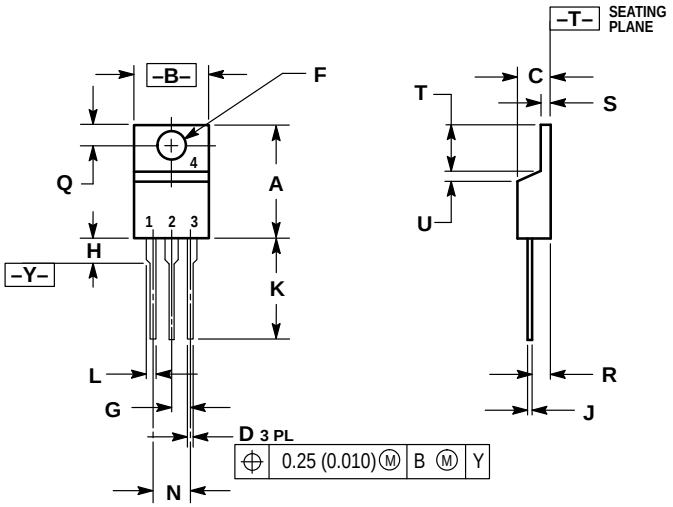
This document contains information on a new product. Specifications and information are subject to change without notice.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–to–Emitter Breakdown Voltage (V_{GE} = 0 Vdc, I_C = 250 μAdc)		B_{VCES}	600	—	—	Vdc
Temperature Coefficient (Positive)			—	870	—	mV/°C
Emitter–to–Collector Breakdown Voltage (V_{GE} = 0 Vdc, I_{EC} = 100 mAdc)		B_{VECS}	15	—	—	Vdc
Zero Gate Voltage Collector Current		I_{CES}				μAdc
(V_{CE} = 600 Vdc, V_{GE} = 0 Vdc)			—	—	100	
(V_{CE} = 600 Vdc, V_{GE} = 0 Vdc, T_J = 125°C)			—	—	2500	
Gate–Body Leakage Current (V_{GE} = ± 20 Vdc, V_{CE} = 0 Vdc)		I_{GES}	—	—	250	nAdc
ON CHARACTERISTICS (1)						
Collector–to–Emitter On–State Voltage		$V_{CE(on)}$				Vdc
(V_{GE} = 15 Vdc, I_C = 1.5 Adc)			—	1.58	2.06	
(V_{GE} = 15 Vdc, I_C = 1.5 Adc, T_J = 125°C)			—	1.46	—	
(V_{GE} = 15 Vdc, I_C = 3 Adc)			—	2.02	2.77	
Gate Threshold Voltage		$V_{GE(th)}$				Vdc
(V_{CE} = V_{GE}, I_C = 1 mAdc)			4.0	6.0	8.0	
Threshold Temperature Coefficient (Negative)			—	10	—	mV/°C
Forward Transconductance (V_{CE} = 10 Vdc, I_C = 3 Adc)		g_{fe}	—	1.3	—	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{CE} = 25 Vdc, V_{GE} = 0 Vdc, f = 1.0 MHz)	C_{ies}	—	362	—	pF
Output Capacitance		C_{oes}	—	36	—	
Transfer Capacitance		C_{res}	—	3	—	
SWITCHING CHARACTERISTICS (1)						
Turn–On Delay Time	(V_{CC} = 360 Vdc, I_C = 3 Adc, V_{GE} = 15 Vdc, L = 300 μH, R_G = 20 Ω, T_J = 25°C) Energy losses include “tail”	$t_{d(on)}$	—	tbd	—	ns
Rise Time		t_r	—	tbd	—	
Turn–Off Delay Time		$t_{d(off)}$	—	60	—	
Fall Time		t_f	—	218	—	
Turn–Off Switching Loss		E_{off}	—	0.09	0.14	mJ
Turn–On Delay Time	(V_{CC} = 360 Vdc, I_C = 3 Adc, V_{GE} = 15 Vdc, L = 300 μH, R_G = 20 Ω, T_J = 125°C) Energy losses include “tail”	$t_{d(on)}$	—	tbd	—	ns
Rise Time		t_r	—	tbd	—	
Turn–Off Delay Time		$t_{d(off)}$	—	tbd	—	
Fall Time		t_f	—	tbd	—	
Turn–Off Switching Loss		E_{off}	—	0.13	—	mJ
Gate Charge	(V_{CC} = 360 Vdc, I_C = 3 Adc, V_{GE} = 15 Vdc)	Q_T	—	14	—	nC
		Q_1	—	6	—	
		Q_2	—	4	—	
INTERNAL PACKAGE INDUCTANCE						
Internal Emitter Inductance (Measured from the emitter lead 0.25″ from package to emitter bond pad)		L_E	—	7.5	—	nH

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.560	0.625	14.23	15.87
B	0.380	0.420	9.66	10.66
C	0.140	0.190	3.56	4.82
D	0.020	0.045	0.51	1.14
F	0.139	0.155	3.53	3.93
G	0.100 BSC		2.54 BSC	
H	——	0.280	——	7.11
J	0.012	0.045	0.31	1.14
K	0.500	0.580	12.70	14.73
L	0.045	0.070	1.15	1.77
N	0.200 BSC		5.08 BSC	
Q	0.100	0.135	2.54	3.42
R	0.080	0.115	2.04	2.92
S	0.020	0.055	0.51	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 221A–06
TO–220AB
ISSUE Y

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